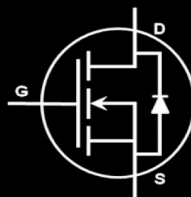


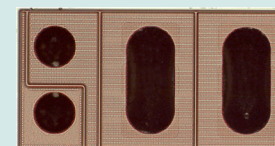
EPC2012C – Enhancement Mode Power Transistor

 V_{DS} , 200 V $R_{DS(on)}$, 100 mΩ I_D , 5 A

NEW PRODUCT



Gallium Nitride is grown on Silicon Wafers and processed using standard CMOS equipment leveraging the infrastructure that has been developed over the last 55 years. GaN's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR} . The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.



EPC2012C eGaN® FETs are supplied only in passivated die form with solder bars

Applications

- High Speed DC-DC conversion
- Class D Audio
- High Frequency Hard-Switching and Soft-Switching Circuits

Benefits

- Ultra High Efficiency
- Ultra Low $R_{DS(on)}$
- Ultra low Q_G
- Ultra small footprint

www.epc-co.com/epc/Products/eGaNfets/EPC2012C.aspx

Maximum Ratings

V_{DS}	Drain-to-Source Voltage	200	V
I_D	Continuous ($T_A = 25^\circ\text{C}$, $R_{\theta JA} = 26$)	5	A
	Pulsed (25°C , $T_{Pulse} = 300 \mu\text{s}$)	22	
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
T_J	Operating Temperature	-40 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-40 to 150	

Static Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-to-Source Voltage	$V_{GS} = 0\text{ V}$, $I_D = 60 \mu\text{A}$	200			V
I_{DSS}	Drain Source Leakage	$V_{DS} = 160\text{ V}$, $V_{GS} = 0\text{ V}$		10	50	μA
I_{GSS}	Gate-to-Source Forward Leakage	$V_{GS} = 5\text{ V}$		0.2	1	mA
	Gate-to-Source Reverse Leakage	$V_{GS} = -4\text{ V}$		10	50	μA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1\text{ mA}$	0.8	1.4	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	$V_{GS} = 5\text{ V}$, $I_D = 3\text{ A}$		70	100	mΩ

Source-Drain Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise stated)

V_{SD}	Source-Drain Forward Voltage	$I_S = 0.5\text{ A}$, $V_{GS} = 0\text{ V}$		1.9		V
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All measurements were done with substrate shorted to source.

Thermal Characteristics

		TYP	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.2	$^\circ\text{C/W}$
$R_{\theta JB}$	Thermal Resistance, Junction to Board	12.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1)	85	$^\circ\text{C/W}$

Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.
See http://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details.

Dynamic Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{ISS}	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}$		100	140	pF
C_{OSS}	Output Capacitance			64	85	
C_{RSS}	Reverse Transfer Capacitance			0.4	0.6	
R_G	Gate Resistance			0.6		Ω
Q_G	Total Gate Charge	$V_{DS} = 100\text{ V}, I_D = 3\text{ A}, V_{GS} = 5\text{ V}$		1	1.3	nC
Q_{GS}	Gate to Source Charge	$V_{DS} = 100\text{ V}, I_D = 3\text{ A}$		0.3		
Q_{GD}	Gate to Drain Charge			0.2	0.35	
$Q_{G(TH)}$	Gate Charge at Threshold			0.2		
Q_{OSS}	Output Charge	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}$		10	13	
Q_{RR}	Source-Drain Recovery Charge			0		

All measurements were done with substrate shorted to source.

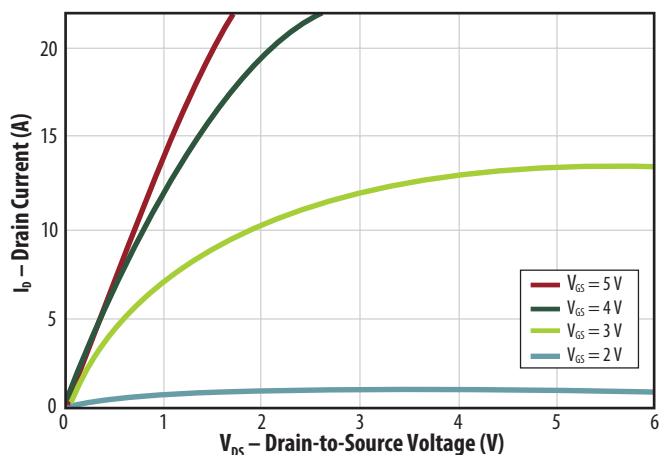
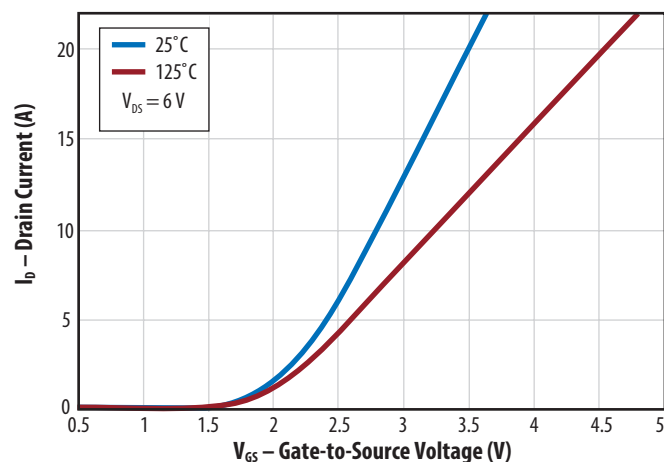
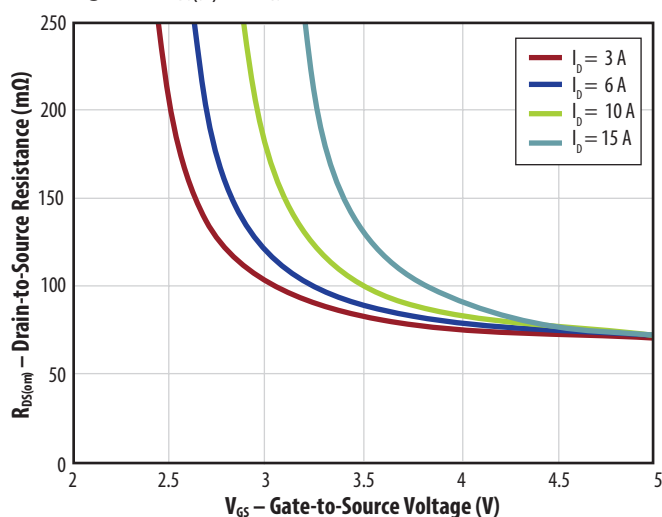
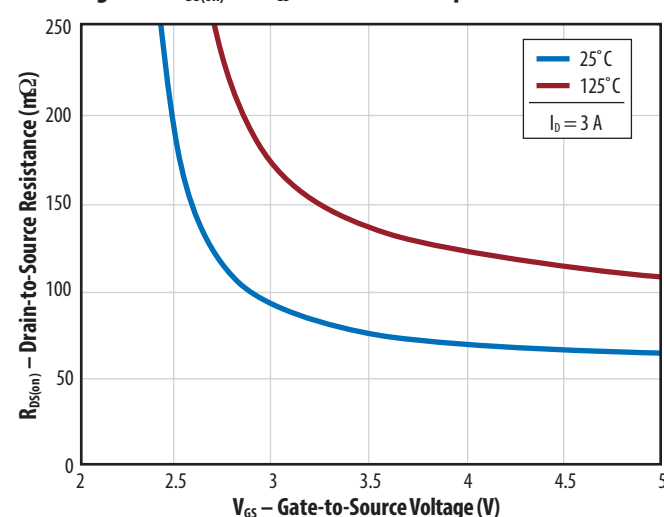
Figure 1: Typical Output Characteristics at 25°C **Figure 2: Transfer Characteristics****Figure 3: $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents****Figure 4: $R_{DS(on)}$ vs. V_{GS} for Various Temperatures**

Figure 5a: Capacitance (Linear Scale)

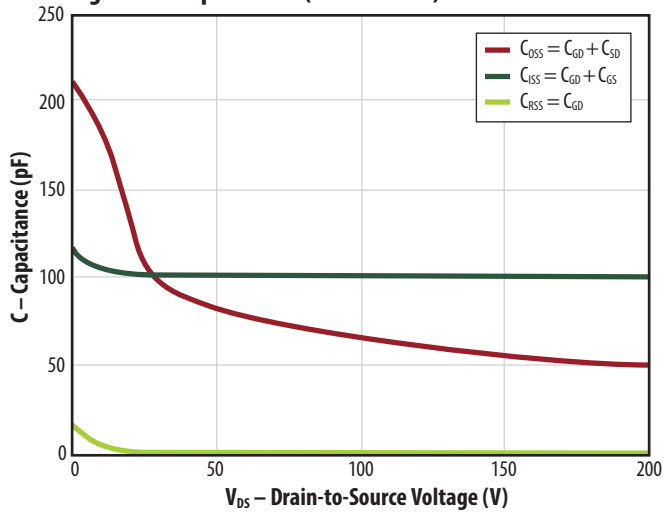


Figure 5b: Capacitance (Log Scale)

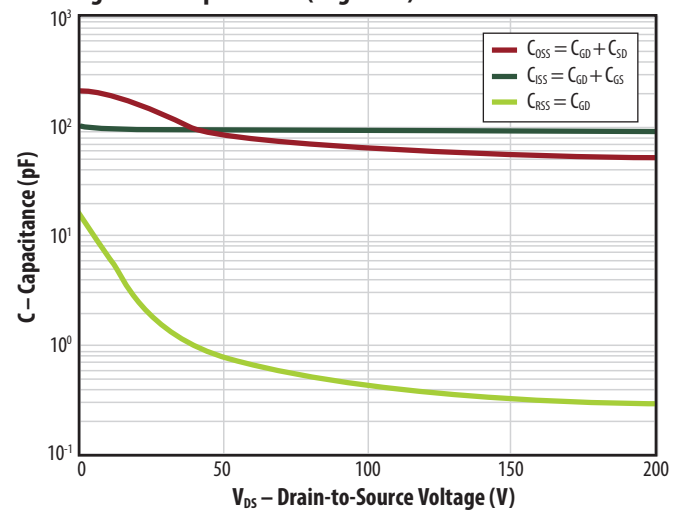


Figure 6: Gate Charge

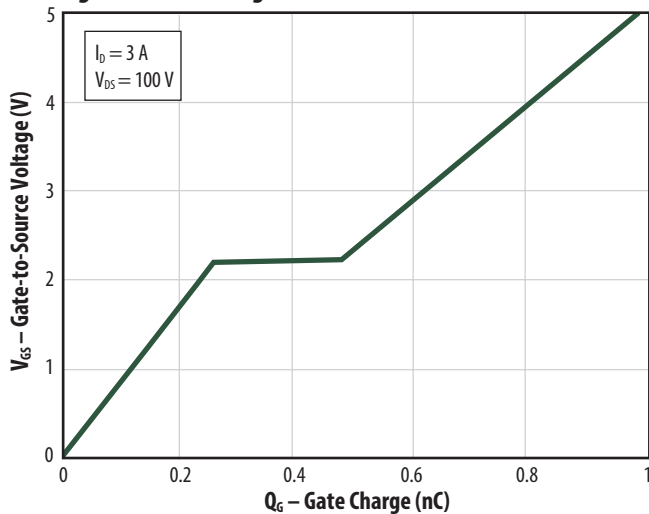


Figure 7: Reverse Drain-Source Characteristics

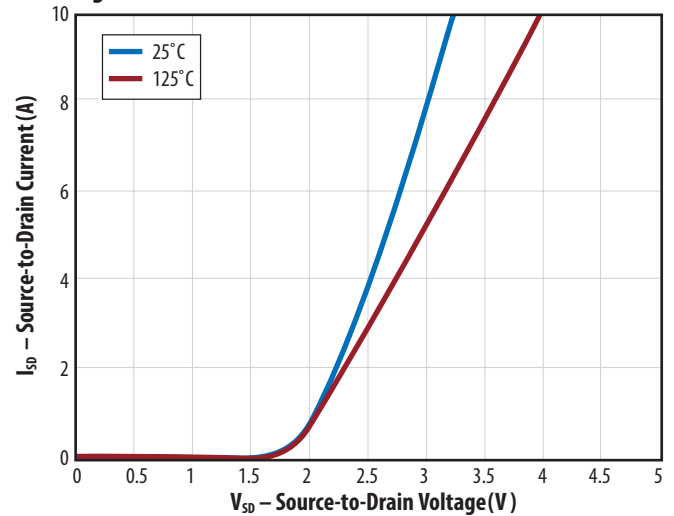


Figure 8: Normalized On Resistance vs. Temperature

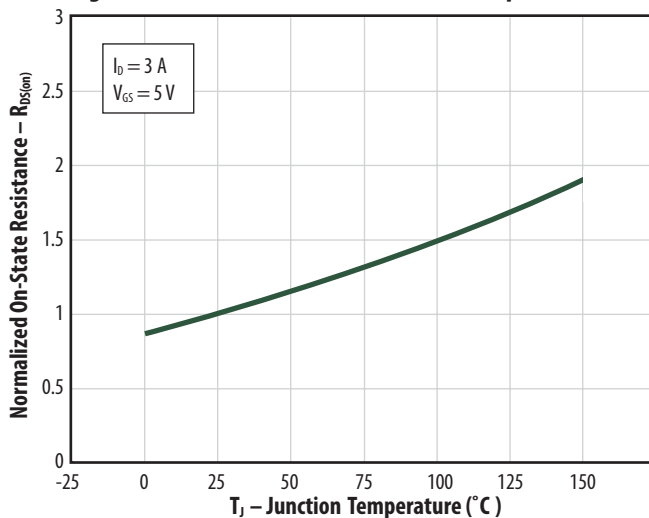
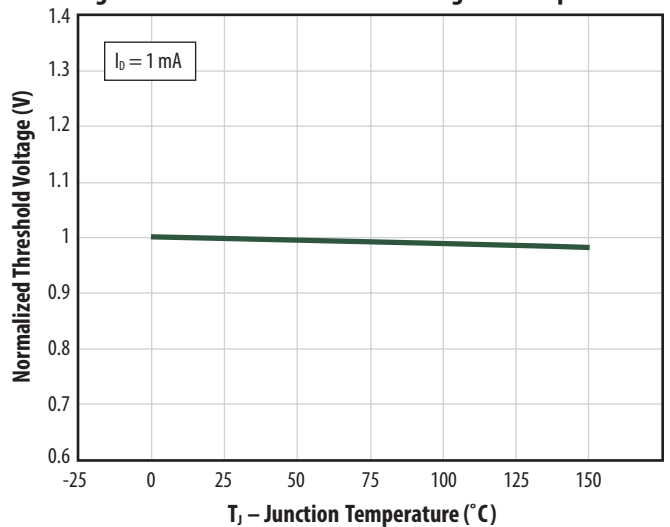


Figure 9: Normalized Threshold Voltage vs. Temperature



All measurements were done with substrate shorted to source.

Figure 10: Gate Current

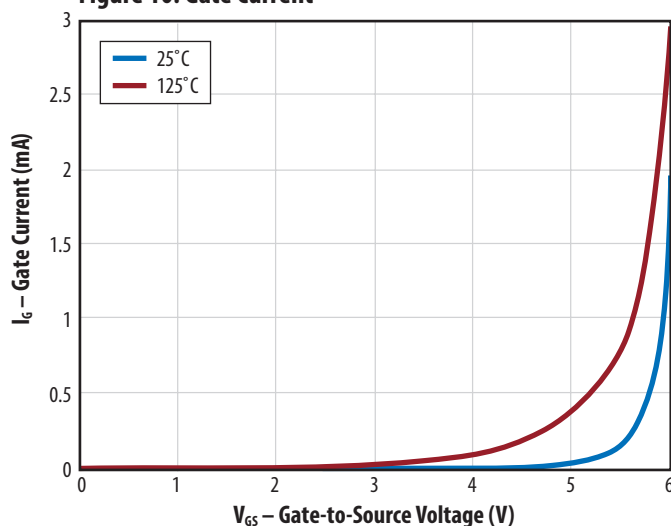


Figure 11: Transient Thermal Response Curves

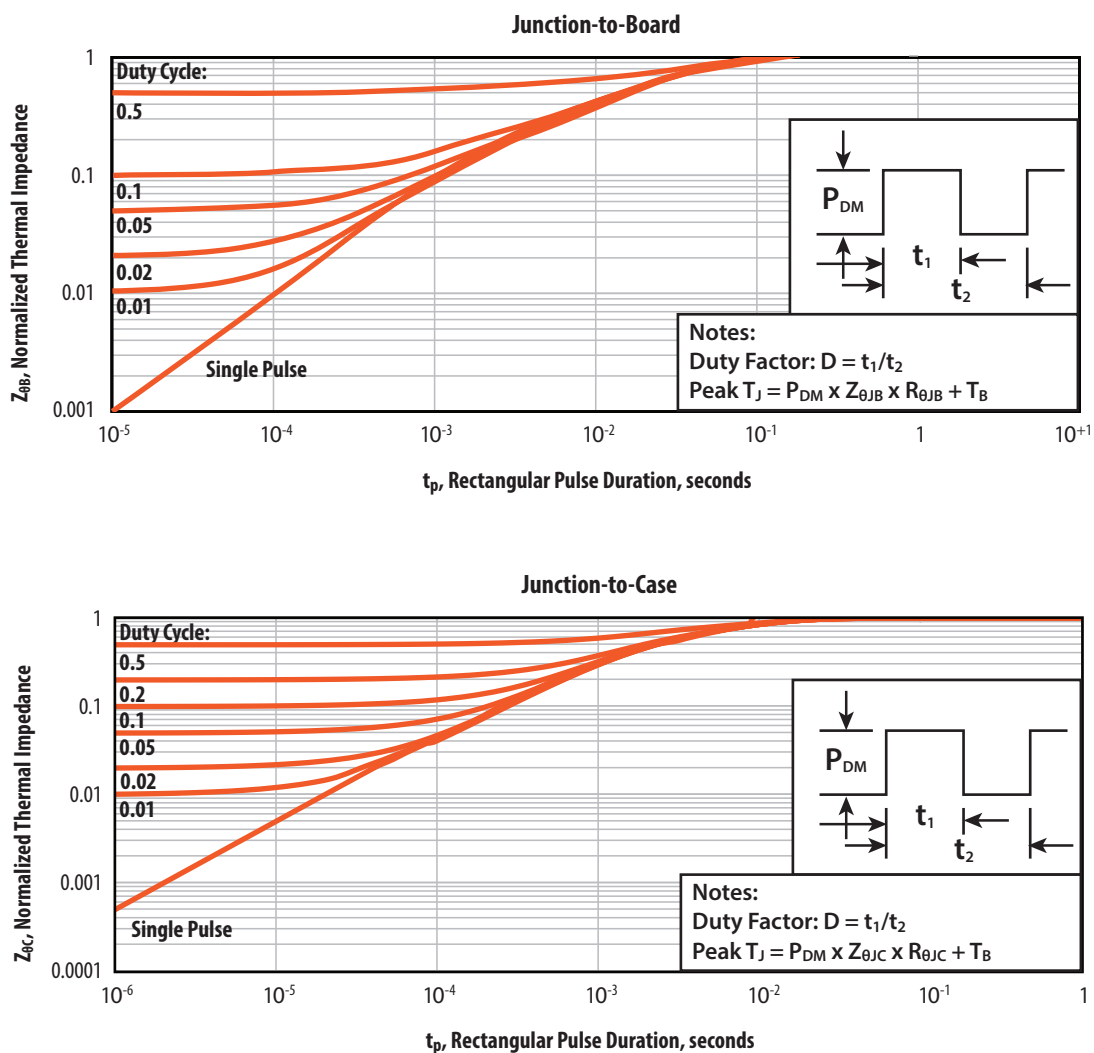
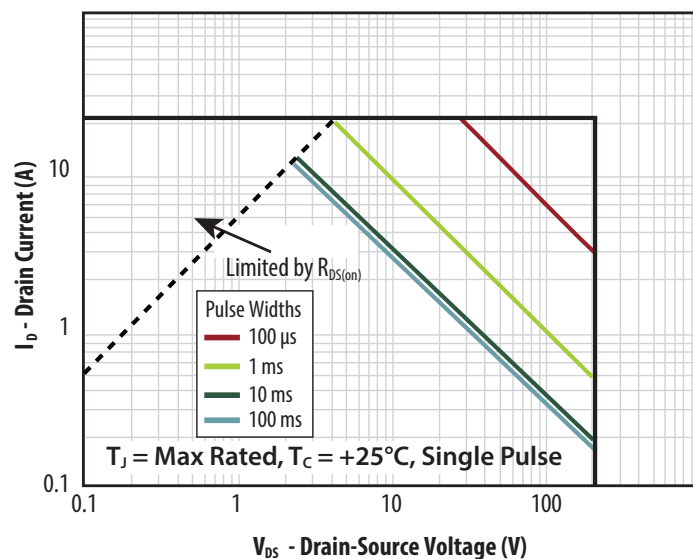
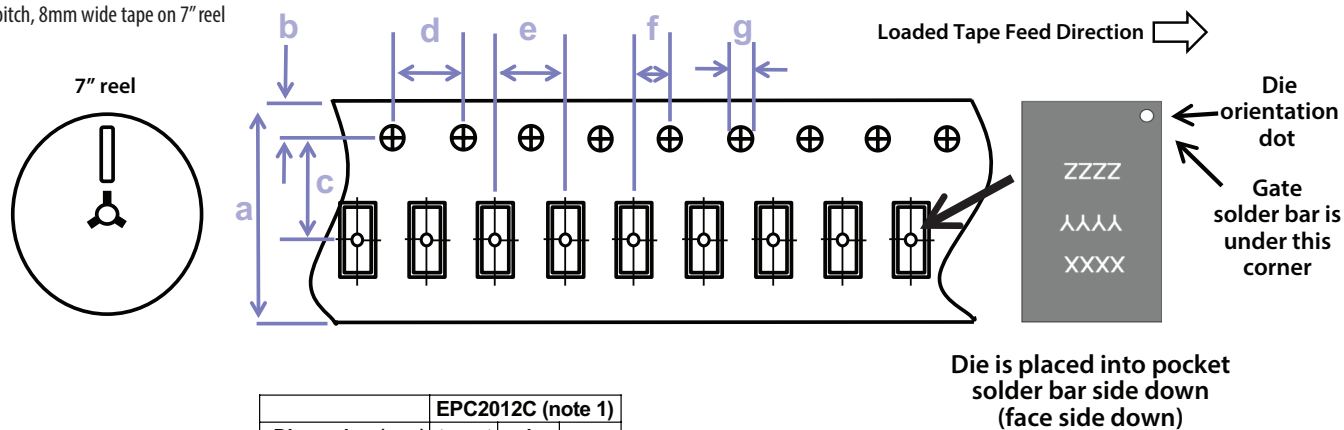


Figure 12: Safe Operating Area



TAPE AND REEL CONFIGURATION

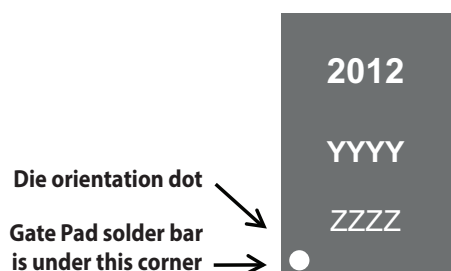
4mm pitch, 8mm wide tape on 7" reel



	EPC2012C (note 1)		
Dimension (mm)	target	min	max
a	8.00	7.90	8.30
b	1.75	1.65	1.85
c (note 2)	3.50	3.45	3.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (note 2)	2.00	1.95	2.05
g	1.5	1.5	1.6

Note 1: MSL1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.
 Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

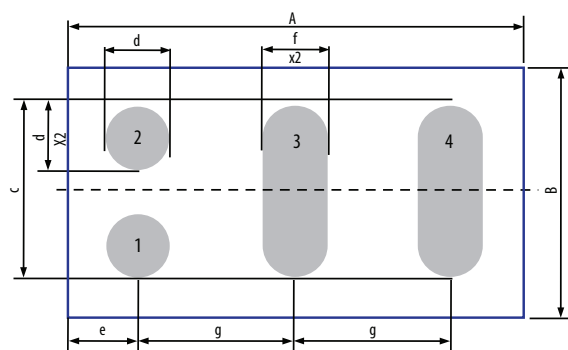
DIE MARKINGS



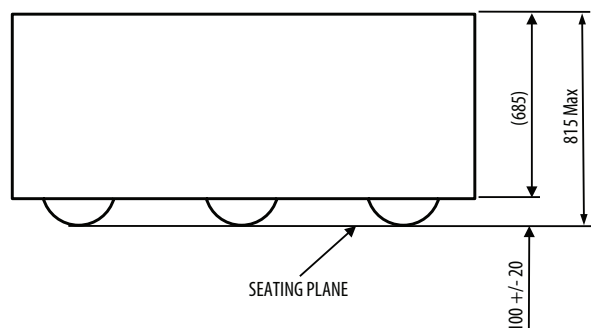
Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking line 2	Lot_Date Code Marking Line 3
EPC2012C	2012	YYYY	ZZZZ

DIE OUTLINE

Solder Bar View



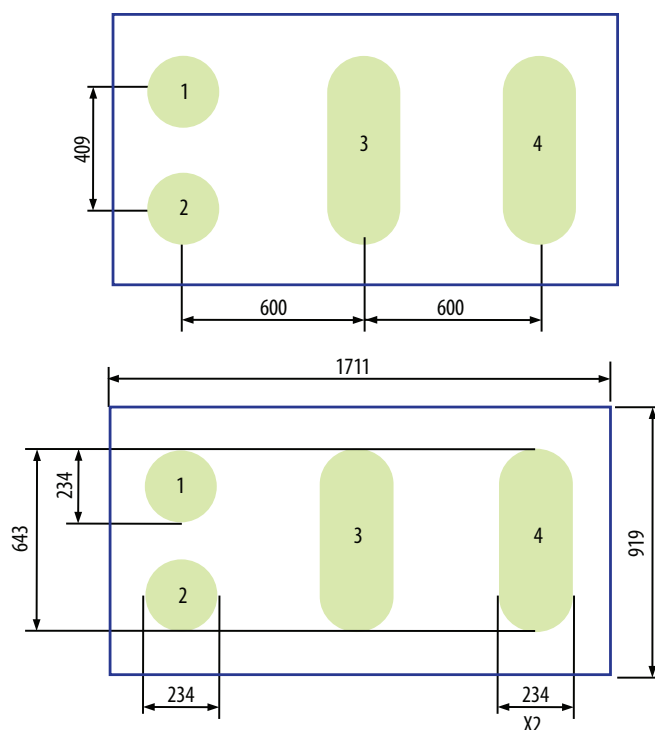
Side View



DIM	MILLIMETERS		
	MIN	Nominal	MAX
A	1.681	1.711	1.741
B	0.889	0.919	0.949
C	0.660	0.663	0.666
d	0.251	0.254	0.257
e	0.230	0.245	0.260
f	0.251	0.254	0.257
g	0.600	0.600	0.600

RECOMMENDED**LAND PATTERN**(units in μm)

The land pattern is solder mask defined



Pad no. 1 is Gate

Pad no. 2 is Substrate

Pad no. 3 is Drain

Pad no. 4 is Source

For assembly recommendations please visit www.epc-co.com/epc/DesignSupport/AssemblyBasics.aspx

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U.S. Patents 8,350,294; 8,404,508; 8,431,960; 8,436,398

Information subject to
change without notice.
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